Zuocheng Zhang

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

13 papers	1,332 citations	11 h-index	13 g-index
13 ext. papers	1,517 ext. citations	13.1 avg, IF	3.68 L-index

#	Paper	IF	Citations
13	Quantum Hall Effect in Electron-Doped Black Phosphorus Field-Effect Transistors. *Nano Letters*, **2018**, 18, 6611-6616	11.5	31
12	Strain-Modulated Bandgap and Piezo-Resistive Effect in Black Phosphorus Field-Effect Transistors. *Nano Letters*, **2017**, 17, 6097-6103	11.5	88
11	Magnetic quantum phase transition in Cr-doped Bi(SeTe) driven by the Stark effect. *Nature Nanotechnology*, **2017**, 12, 953-957	28.7	13
10	Direct observation of the layer-dependent electronic structure in phosphorene. *Nature Nanotechnology*, **2017**, 12, 21-25	28.7	473
9	Field-effect modulation of anomalous Hall effect in diluted ferromagnetic topological insulator epitaxial films. *Science China: Physics, Mechanics and Astronomy*, **2016**, 59, 1	3.6	11
8	Quantum Hall effect in black phosphorus two-dimensional electron system. *Nature Nanotechnology* , **2016**, 11, 593-7	28.7	289
7	Thickness Dependence of the Quantum Anomalous Hall Effect in Magnetic Topological Insulator Films. *Advanced Materials*, **2016**, 28, 6386-90	24	50
6	Disentangling the magnetoelectric and thermoelectric transport in topological insulator thin films. *Physical Review B*, **2015**, 91,	3.3	28
5	Zeeman effect of the topological surface states revealed by quantum oscillations up to 91 Tesla. *Physical Review B*, **2015**, 92,	3.3	7
4	Electrically tuned magnetic order and magnetoresistance in a topological insulator. *Nature Communications*, **2014**, 5, 4915	17.4	42
3	Chemical-potential-dependent gap opening at the Dirac surface states of Bi2Se3 induced by aggregated substitutional Cr atoms. *Physical Review Letters*, **2014**, 112, 056801	7.4	84
2	Transport properties of Sb2Te3/Bi2Te3 topological insulator heterostructures. *Physica Status Solidi - Rapid Research Letters*, **2013**, 7, 142-144	2.5	12
1	Electron interaction-driven insulating ground state in Bi2Se3 topological insulators in the two-dimensional limit. *Physical Review B*, **2011**, 83,	3.3	204